

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	7	wajda near cory.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	15	dip near anthony.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	2	furukawa near toshihara.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	34170	(oxynitride or oxy-nitride or sion)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	21714	(oxynitride or oxy-nitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	4560	(oxynitride or oxy-nitride) near25 (wafer or substrate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	2615	((oxynitride or oxy- nitride) near25 (wafer or substrate)) near25 (oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	2	((oxynitride or oxy- nitride) near25 (wafer or substrate)) near25 (self- limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	3	((oxynitride or oxy-nitride) near25 (wafer or substrate)) same (self-limit\$3 near oxid\$5)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
10	BRS	L10	10	((oxynitride or oxy-nitride) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
11	BRS	L11	10	((oxynitride or oxy near nitride) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
12	BRS	L12	0	((sion) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB

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13	BRS	L13	0	((sio) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	0	((sio2) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	0	((siosub.2) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	23	((sio.sub.2) near25 (wafer or substrate)) and (self-limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	3	((("sio.sub.xn.sub.y") near25 (wafer or substrate)) and (self- limit\$3 near oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	119	((("sio.sub.xn.sub.y") near25 (wafer or substrate)) and (oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	0	((("sio.sub.xn.sub.y") near25 (wafer or substrate)) near25 (pressure) near15 (chamber) and (oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	4	((("sio.sub.xn.sub.y") near25 (wafer or substrate)) near25 (pressure) and (oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	5	((("sio.sub.xn.sub.y") near25 (wafer or substrate)) near25 (chamber) and (oxid\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	290	((oxynitride or oxy near nitride) near25 (wafer or substrate)) near25 (oxidation)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	55	22 and (chamber near15 pressure)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L25	1	24 and (chamber near15 pressure)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L24	10	((oxy-nitride) near25 (wafer or substrate)) near25 (oxidation)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	0	22 and (chamber near15 pressure near25 nirogen- containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	4	22 and (chamber near15 pressure near25 containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
28	BRS	L28	285	((oxynitride or oxy- nitride) near25 (wafer or substrate)) near25 (oxidation)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

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29	BRS	L29	37	28 and (nitrogen-containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
30	BRS	L30	15	((oxynitride or oxy-nitride) near25 (wafer or substrate)) near25 (oxidation) near25 (nitrogen-containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L31	2	((oxynitride or oxy-nitride) near25 (chamber near35 substrate)) near25 (oxidation) near25 (nitrogen-containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
32	BRS	L32	0	((oxynitride or oxy-nitride) near25 (chamber near35 substrate)) near25 (oxidation) near25 (oxygen-containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B



	Type	L #	Hits	Search Text	DBs
33	BRS	L33	2	((oxynitride or oxy-nitride) near25 (chamber near35 substrate)) near25 (oxidation) near25 (nitr\$5-containing)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
34	BRS	L34	15	((oxynitride or oxy-nitride) near25 (substrate)) near25 (oxidation) near25 (nitr\$5-containing)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
35	BRS	L35	8	34 and (chamber)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB
36	BRS	L36	15	34 and (pressure)	US-PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TDB

	Type	L #	Hits	Search Text	DBs
37	BRS	L37	15	((oxynitride or oxy near nitride) near25 (substrate)) near25 (oxidation) near25 (nitr\$5- containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
38	BRS	L38	15	37 and (pressure)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
39	BRS	L39	4	38 and (process\$3 near chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
40	BRS	L40	11088	(controller) near25 (processing near system)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
41	BRS	L41	37	(controller) near25 (processing near system) near25 (substrate near holder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
42	BRS	L42	0	41 and (oxynitride near layer)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
43	BRS	L43	1	41 and (oxynitride)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
44	BRS	L45	152	(controller) near25 (chamber) near25 (substrate near holder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
45	BRS	L46	0	(controller) near25 (batch near3 chamber) near25 (substrate near holder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
46	BRS	L47	1	(batch near3 chamber) near25 (substrate near holder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
47	BRS	L48	70	(batch near3 chamber) near25 (pump\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
48	BRS	L49	0	(batch near3 chamber) near25 (monitor\$3 near15 pump\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
49	BRS	L50	0	(batch near3 chamber) near25 (monitor\$3 near35 pump\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
50	BRS	L51	541	(batch near3 chamber) near25 (process)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
51	BRS	L52	107	(batch near3 chamber) near25 (process near chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
52	BRS	L53	16	(batch near3 chamber) near25 (process near chamber) near25 (single near5 chamber)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
53	BRS	L44	18	(controller) near25 (processing near chamber) near25 (substrate near holder)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
9			US 6610614 B2	Method for uniform nitridization of ultra-thin silicon dioxide layers in transistor gates
10			US 6548366 B2	Method of two-step annealing of ultra-thin silicon dioxide layers for uniform nitrogen profile
11			US 6503846 B1	Temperature spike for uniform nitridization of ultra-thin silicon dioxide layers in transistor gates
12			US 6426255 B1	Process for making a semiconductor integrated circuit device having a dynamic random access memory
13			US 6087229 A	Composite semiconductor gate dielectrics

	U	1	Document ID	Title
14			US 6033998 A	Method of forming variable thickness gate dielectrics
15			US 20050026459 A	Method for forming semiconductor microstructure e.g. for gate electrode microstructure, involves setting partial pressure of nitrogen-containing oxidizing gas passed to process chamber containing substrate, to specific value